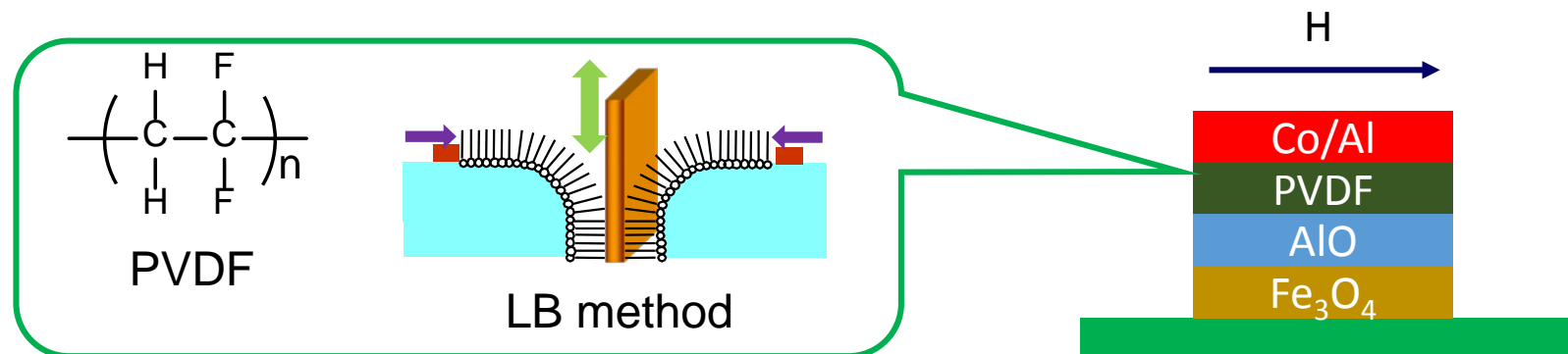


強誘電性高分子超薄膜による室温磁気抵抗効果

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Room temperature magnetoresistance effects in ferroelectric poly(vinylidene fluoride) spin valves

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Langmuir-Blodgett (LB) 法により作製される強誘電性高分子PVDFをバリアー層としてスピン輸送素子が構築された。PVDF LB膜3層からなるデバイスに対し、室温で2.5%の磁気抵抗比を超える磁気抵抗効果が観測された。

Poly(vinylidene fluoride) (PVDF) Langmuir-Blodgett (LB) films were used as a barrier layer for spin transport device application. The magnetoresistance (MR) effect with more than 2.5 % MR ratio at room temperature was observed for the 3-layer PVDF sample.